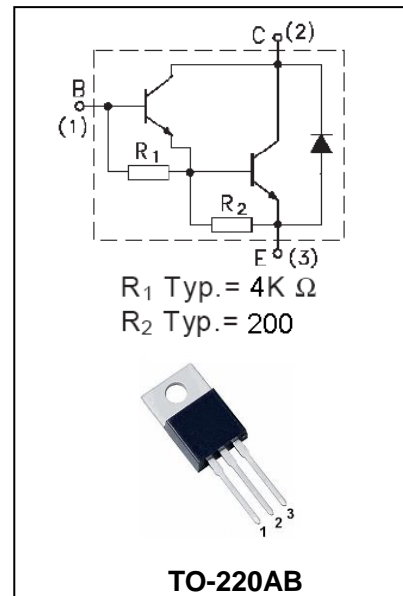


FEATURES

- Monolithic Construction With Built in Base -Emitter Shunt Resistors
- Complementary to TIP117
- High DC Current Gain: $h_{FE}=1000@V_{CE}=4V,I_C=1A$
- Low Collector-Emitter Saturation Voltage
- Industrial Use



Ordering Information

Part Number	Package	Shipping	Marking Code
TIP112	TO-220AB	50 pcs / Tube	TIP112

MAXIMUM RATING operating temperature range applies unless otherwise specified

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	100	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	DC	2
		Pulse	4
I_B	Base Current	50	mA
P_C	Collector Dissipation	$T_a=25^\circ\text{C}$	2
		$T_C=25^\circ\text{C}$	50
T_j, T_{stg}	Junction and Storage Temperature	-65 to +150	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-emitter Sustaining Voltage	$V_{CEO(SUS)}$	$I_C=30mA, I_B=0$	100			V
Collector Cut-off Current	I_{CEO}	$V_{CE}=50V, I_B=0$			2	mA
Collector Cut-off Current	I_{CBO}	$V_{CB}=100V, I_E=0$			1	mA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$			2	mA
DC Current Gain	h_{FE}	$V_{CE}=4V, I_C=1A$ $V_{CE}=4V, I_C=2A$	1000 500			
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=2A, I_B=8mA$			2.5	V
Base-emitter on Voltage	$V_{BE(on)}$	$V_{CE}=4V, I_C=2A$			2.8	V
Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0,$ $f=0.1MHz$			100	pF

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

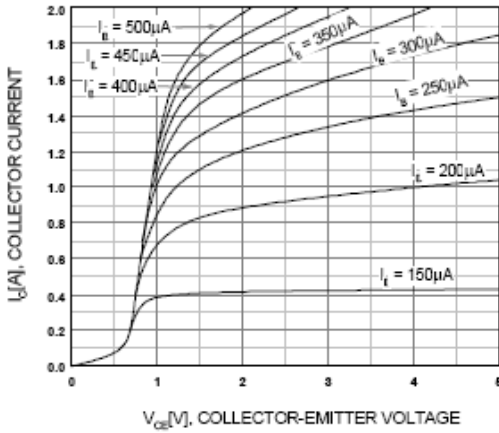


Figure 1. Static Characteristic

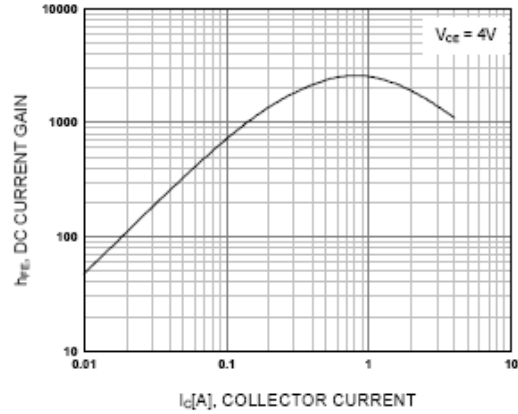


Figure 2. DC current Gain

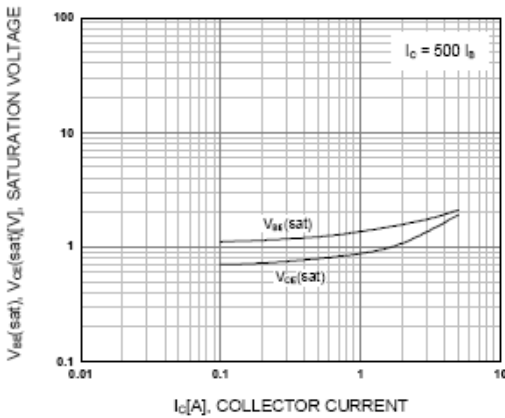


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

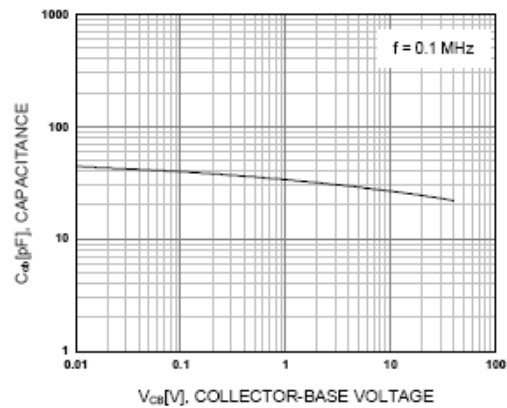


Figure 4. Collector Output Capacitance

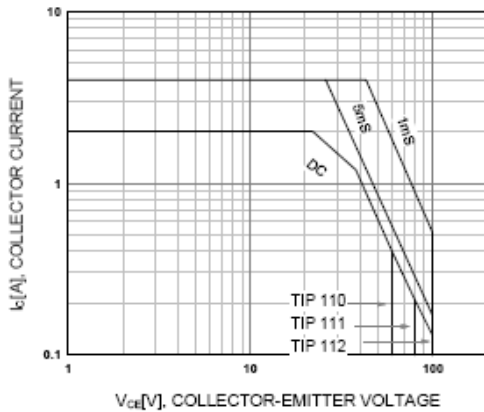


Figure 5. Safe Operating Area

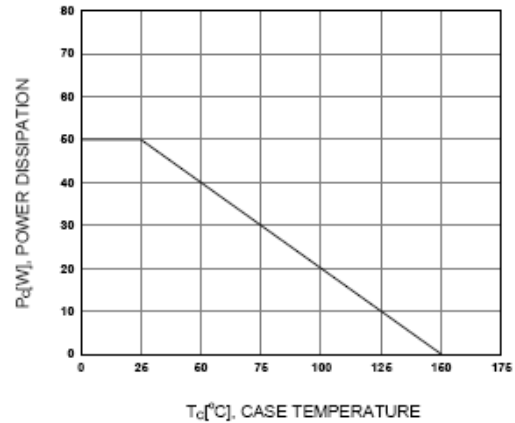


Figure 6. Power Derating

PACKAGE OUTLINE

Plastic surface mounted package

TO-220AB

